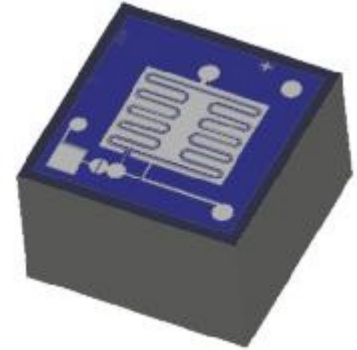


### FEATURES

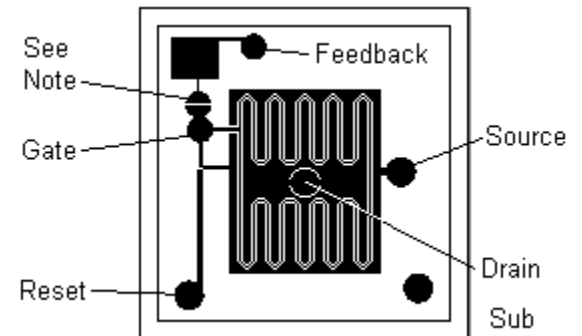
- Ultra Low Noise
  - Less than 1.5nV @ 1KHz, 20°C
- Free of Generation Recombination Noise
- Excellent  $g_m$  to  $C_{gs}$  Ratio
  - $g_m=28mS$ ,  $C_{gs}=4pF$ , 20°C
- 4-Terminal
- N-Channel
- Available in Die and Other Packages



Noise Characteristics Units in nV/√Hz	Typ	Max	Test Condition	Temp
1KHz	1.1		$V_{ds}=4V, I_d=5mA$	20°C
10KHz	0.8		$V_{ds}=4V, I_d=5mA$	20°C
100KHz	0.8		$V_{ds}=4V, I_d=5mA$	20°C
1KHz	0.9	1.3	$V_{ds}=4V, I_d=5mA$	-100°C
10KHz	0.6	1.0	$V_{ds}=4V, I_d=5mA$	-100°C
100KHz	0.6	1.0	$V_{ds}=4V, I_d=5mA$	-100°C

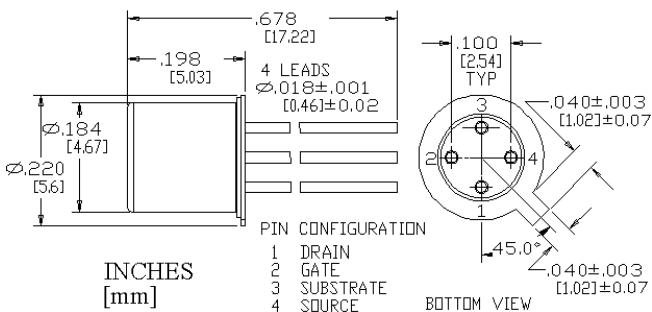
Die Size 0.80mm x 0.80mm x 0.50mm

Static Characteristics		Min	Typ	Max	Unit	Test Condition
Gate to Source Breakdown	$BV_{gss}$	20	26		V	$V_{ds}=0V, I_g=1\mu A, V_{sub}=0V$
Reverse Leakage Current	$I_{sub}$ $I_{gss}$		0.4		pA	$V_{reverse} = -10V$
Gate to Source Cutoff Voltage	$V_{gs}$		10		V	$V_{sub}=0V, I_d=1nA$
Drain Saturation Current	$I_{dss}$		300		mA	$V_{sub}=0V, V_{gs}=0V$
Dynamic Characteristics						
Transconductance	$g_m$		28 40		mS	$V_{ds}=4V, I_d=5mA, 20^\circ C$ $V_{ds}=4V, I_d=5mA, -100^\circ C$
Gate to Source Capacitance	$C_{gs}$		4		pF	$V_{gs}=0V, V_{ds}=4V, I_d=5mA$

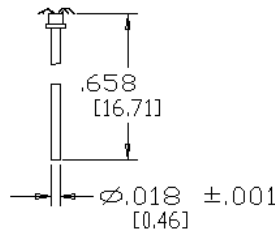


The bottom gate on this 4 terminal JFET is the substrate.

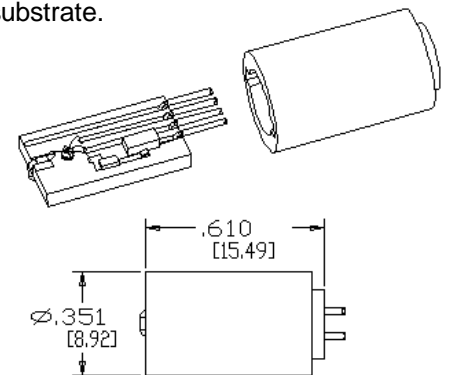
### AVAILABLE JFET PACKAGE:



TO-72 PACKAGE



NAILHEAD FLYING LEADS



TEFLON PACKAGE